

**POLISHING LIQUID FOR POLISHING COMPOUND SEMICONDUCTOR
SUBSTRATE**

ABSTRACT

A polishing liquid for polishing a compound semiconductor substrate includes an aqueous solution in which a permanganate is dissolved, and abrasive grains which are dispersed in the aqueous solution and an electrokinetic potential (zeta potential) of which is plus. Preferably, the polishing liquid has a pH of 3 to 7. In addition, preferably, a concentration of the permanganate is not less than 2.5 wt%, and a concentration of the abrasive grains is not less than 4.5 wt%. Besides, preferably, the abrasive grains include silica grains having an average primary grain diameter of 12 nm to 60 nm.

[FIG. 1]